AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

Claims 1-13 (cancelled)

14. (original) A method of manufacturing a semiconductor device, comprising the steps of:

(a) providing a semiconductor chip, said semiconductor chip having a main surface and a plurality of salient electrodes formed on said main surface;

(b) providing a wiring substrate, said wiring substrate having a thin film base formed by an insulator and also having a plurality of leads corresponding respectively to said plural salient electrodes of said semiconductor chip; and

(c) bonding said plural salient electrodes to said plural leads respectively, wherein, in said wiring substrate provided in said step (b), the pitch of said plural salient electrodes is smaller than the pitch of said

leads at the portions corresponding respectively to the plural salient electrodes,

wherein said plural leads are fixed to said thin film base at their portions to be bonded to said salient electrodes, and

wherein said step (c) includes a step of positioning said wiring substrate and said semiconductor chip to predetermined positions while keeping the two spaced apart from each other, a step of holding the portion of said wiring substrate located around an area where the bonding between said salient electrodes and said leads is performed, grippingly by means of a jig, while keeping the wiring substrate and the semiconductor chip spaced apart from each other, and a step of pushing said wiring substrate by said jig to bring said leads into contact with said salient electrodes.

15. (original) The method according to claim 14, wherein the bonding between said salient electrodes and said leads in said step (c) is performed by forming Au-Sn eutectic bond between the two.

16. (original) The method according to claim 14, wherein the bonding between said salient electrodes and said leads in said step (c) is performed by forming Au-Au bond between the two.

17. (original) The method according to claim 14, wherein the bonding between said salient electrodes and said leads in said step (c) is performed at a temperature of not higher than the glass transition temperature of said insulator which constitutes said thin film base.

18. (original) The method according to claim 14, wherein said thin film base is flexible.

19. (original) The method according to claim 14, wherein the bonding between said salient electrodes and said leads in said step (c) is performed by bringing the salient electrodes and the leads into contact with each other while heating said semiconductor chip to a temperature higher than the temperature of said wiring substrate.

20. (original) The method according to claim 14, wherein the bonding between said salient electrodes and said leads in said step (c) is performed by bringing the salient electrodes and the leads into contact with each other while heating said semiconductor chip to a temperature higher than the temperature of said wiring substrate with use of a jig.

21. (original) The method according to claim 14, wherein the temperature of said jig for heating said semiconductor chip is not lower than the glass transition temperature of said insulator which constitutes said thin film base.

22. (original) The method according to claim 14, wherein the temperature of said wiring substrate before the contact between said salient electrodes and said leads is not higher than the glass transition temperature of said insulator which constitutes said thin film base.